

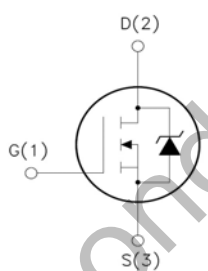
 <p style="font-size: 1.2em; font-weight: bold; margin-top: 10px;">WGP10N20</p> <p>200V N-Channel MOSFET</p> <p>Features:</p> <ul style="list-style-type: none"> <input type="checkbox"/> Low Intrinsic Capacitances. <input type="checkbox"/> Excellent Switching Characteristics. <input type="checkbox"/> Extended Safe Operating Area. <input type="checkbox"/> Unrivalled Gate Charge :Qg= 22nC (Typ.). <input type="checkbox"/> BVDSS=200V, I_D=10A <input type="checkbox"/> R_{DS(on)} : 0.4 Ω (Max) @V_G=10V <input type="checkbox"/> 100% Avalanche Tested 	<p style="text-align: right;">TO-220 </p>  <p style="text-align: center; margin-top: 10px;">1 2 3</p>  <div style="display: flex; justify-content: space-between; margin-top: 10px;"> <div style="width: 45%;"> <p>1.Gate (G)</p> <p>2.Drain (D)</p> <p>3.Source (S)</p> </div> <div style="width: 45%; text-align: right;"> <p>D(2)</p> <p>G(1)</p> <p>S(3)</p> </div> </div>
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Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{DSS}	Drain-Source Voltage	200	V
I _D	Drain Current	T _C =25°C	10
		T _C =100°C	6.3
V _{GS(TH)}	Gate Threshold Voltage	±30	V
E _{AS}	Single Pulse Avalanche Energy (note1)	160	mJ
I _{AR}	Avalanche Current (note2)	10	A
P _D	Power Dissipation (Ta=25°C)	72	W
T _j	Junction Temperature(Max)	150	°C
T _{stg}	Storage Temperature	-55~+150	
TL	Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	300	

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJC}	Thermal Resistance, Junction to Case	-	1.74	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	-	62.5	°C/W

Electrical Characteristics Tc=25°C unless other wise noted						
Symbol	Parameter	Test Condition	Min.	Typ.	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	ID=250 μ A, VGS=0	200	--	--	V
Δ BV _{DSS} / Δ T _J	Breakdown Voltage Temperature Conficient	ID=250 μ A, Reference to 25°C	--	0.2	--	V/°C
IDSS	Zero Gate Voltage Drain Current	Vds=200V, Vgs=0V	--	--	1	μ A
		Vds=160V, Tc=125°C			10	μ A
IGSSF	Gate-body leakage Current, Forward	Vgs=+30V, Vds=0V	--	--	100	nA
IGSSR	Gate-body leakage Current, Reverse	Vgs=-30V, Vds=0V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Date Threshold Voltage	Id=250uA, Vds=Vgs	2	--	4	V
R _{DS(on)}	Static Drain-Source On-Resistance	Id=5A, Vgs=10V	--	--	0.4	Ω
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=25V, VGS=0, f=1.0MHz	--	550	720	pF
Coss	Output Capacitance		--	85	110	pF
Crss	Reverse Transfer Capacitance		--	22	29	pF
Switching Characteristics						
Td(on)	Turn-On Delay Time	VDD=100V, ID=9A, RG=25 Ω (Note 3,4)	--	11	25	nS
Tr	Turn-On Rise Time		--	70	140	nS
Td(off)	Turn-Off Delay Time		--	60	120	nS
Tf	Turn-Off Fall Time		--	65	130	nS
Qg	Total Gate Charge	VDS=160, VGS=10V, ID=9A (Note 3,4)	--	22	30	nC
Qgs	Gate-Source Charge		--	4.0	--	nC
Qgd	Gate-Drain Charge		--	11	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximun Continuous Drain-Source Diode Forward Current		--	--	9	A
I _{SM}	Maximun Plused Drain-Source DiodeForwad Current		--	--	36	A
V _{SD}	Drain-Source Diode Forward Voltage	Id=9A	--	--	1.5	V
trr	Reverse Recovery Time	I _S =9.0A, V _{GS} =0V	--	140	--	nS
Qrr	Reverse Recovery Charge	di _F /dt=100A/ μ s (Note3)	--	0.87	--	μ C
*Notes	1, L=3.0mH, IAS=9.0A, VDD=50V, RG=25Ω, Starting T _J =25°C 2, Repetitive Rating : Pulse width limited by maximum junction temperature 3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2% 4, Essentially Independent of Operating Temperature					

Typical Characteristics

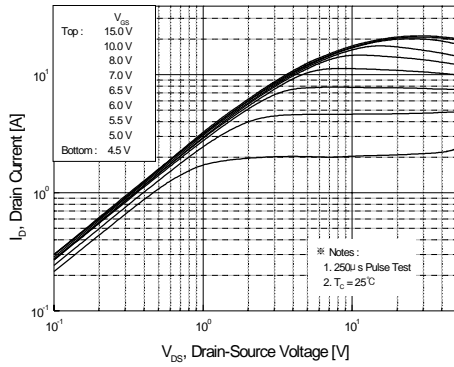


Figure 1. On-Region Characteristics

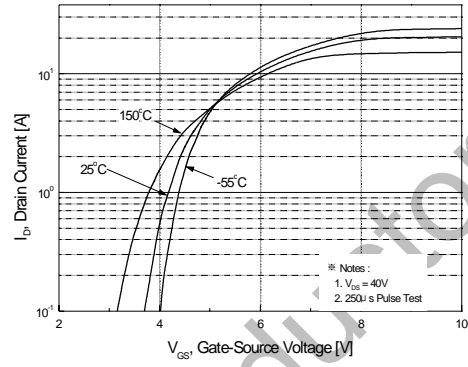


Figure 2. Transfer Characteristics

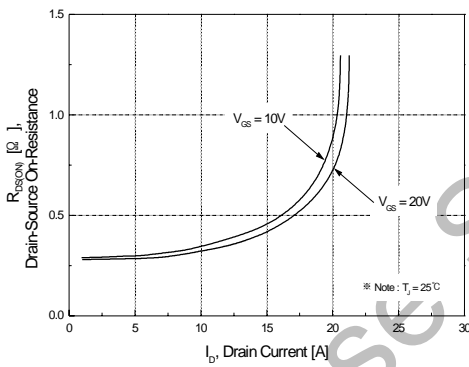


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

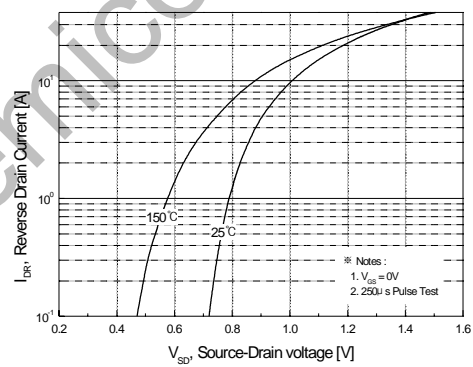


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

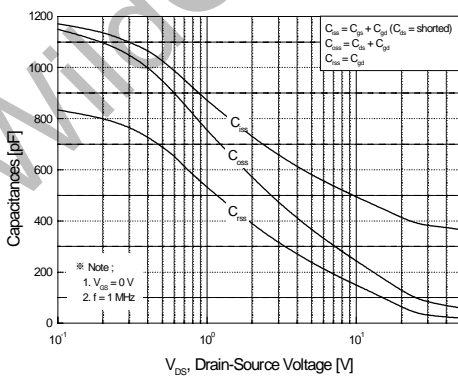


Figure 5. Capacitance Characteristics

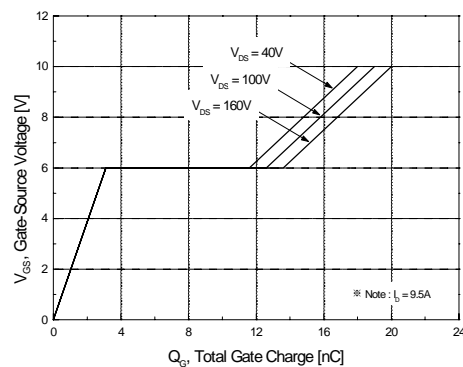


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

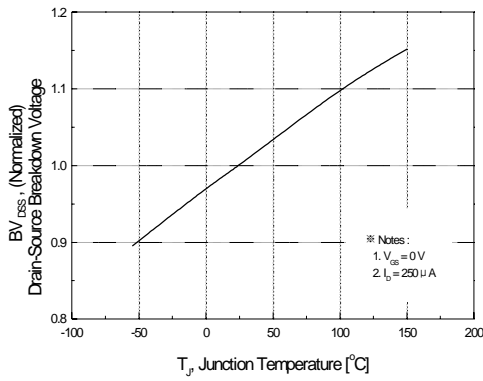


Figure 7. Breakdown Voltage Variation vs Temperature

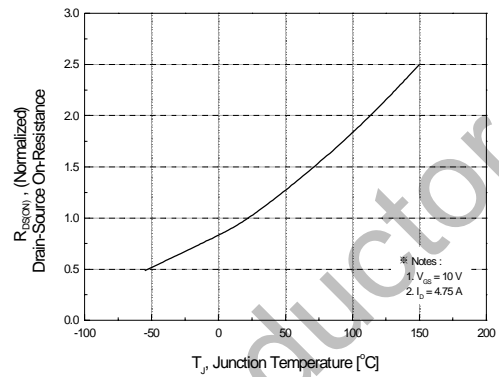


Figure 8. On-Resistance Variation vs Temperature

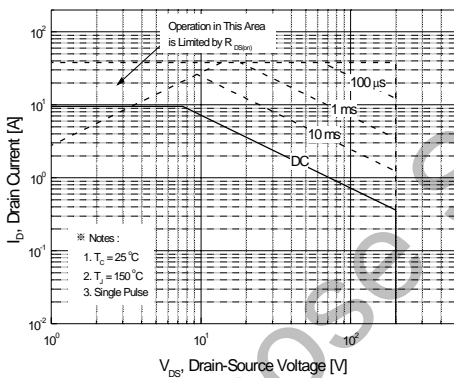


Figure 9-1. Maximum Safe Operating Area

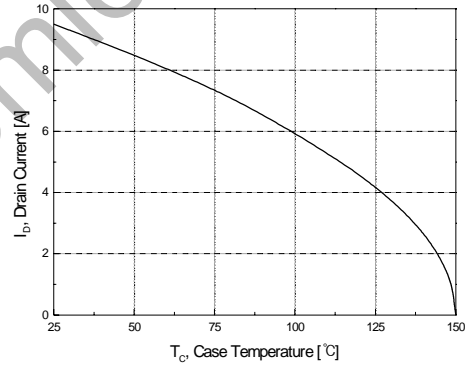


Figure 10. Maximum Drain Current vs Case Temperature

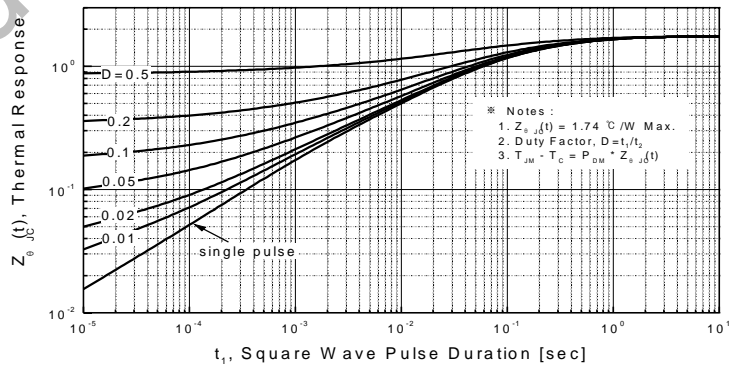
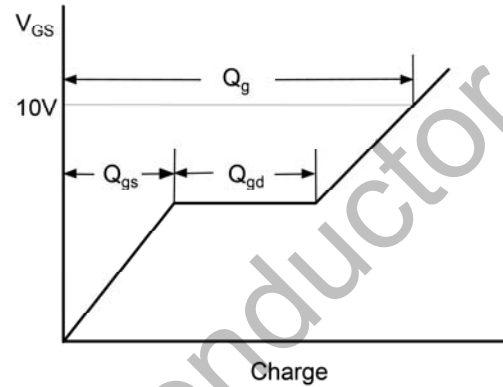
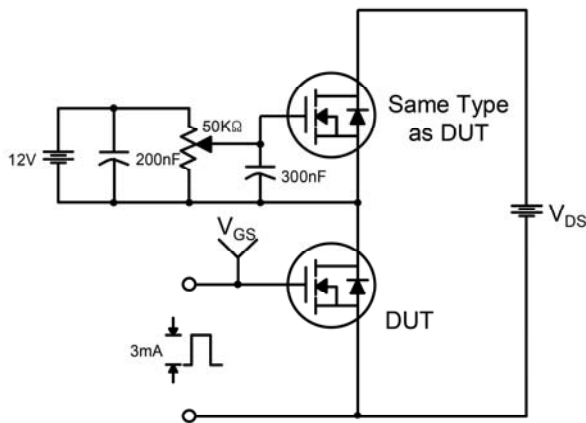
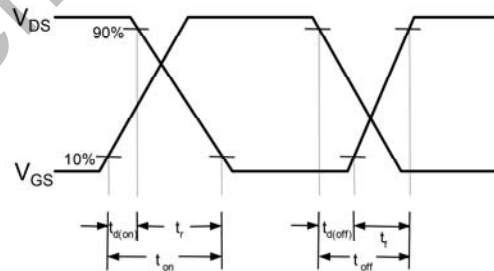
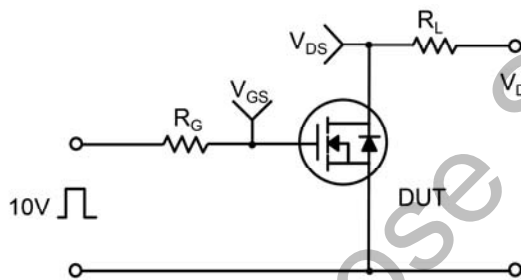


Figure 11-1. Transient Thermal Response Curve

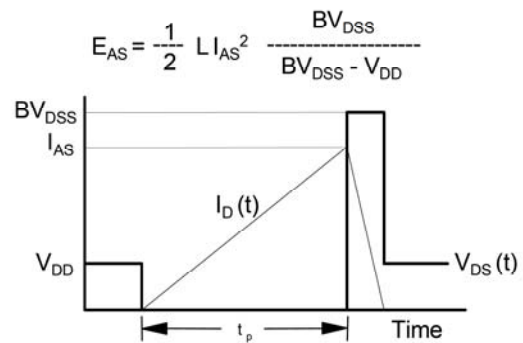
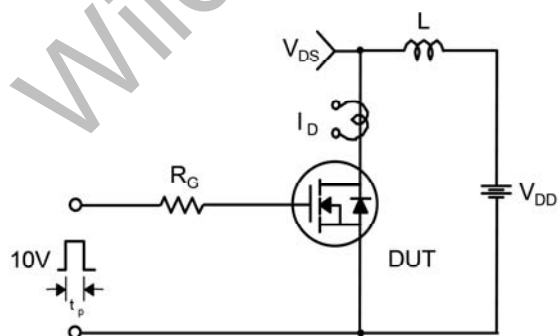
Gate Charge Test Circuit & Waveform



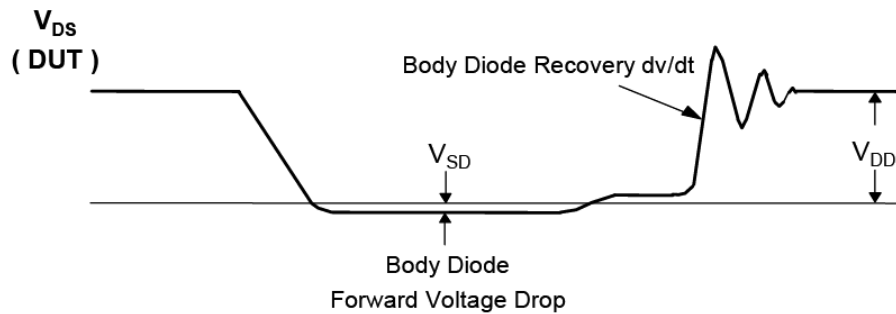
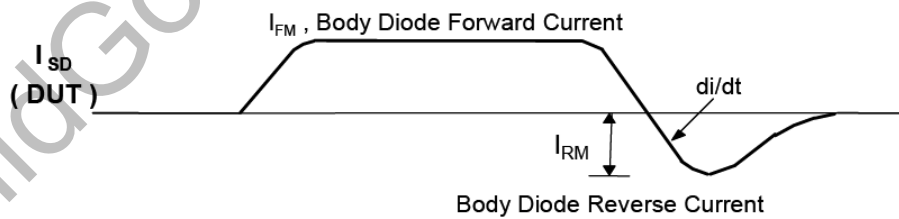
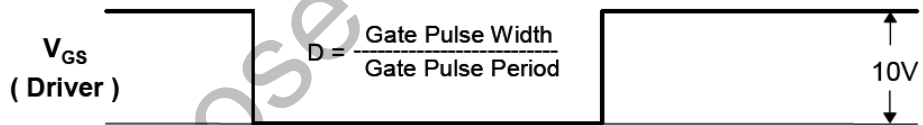
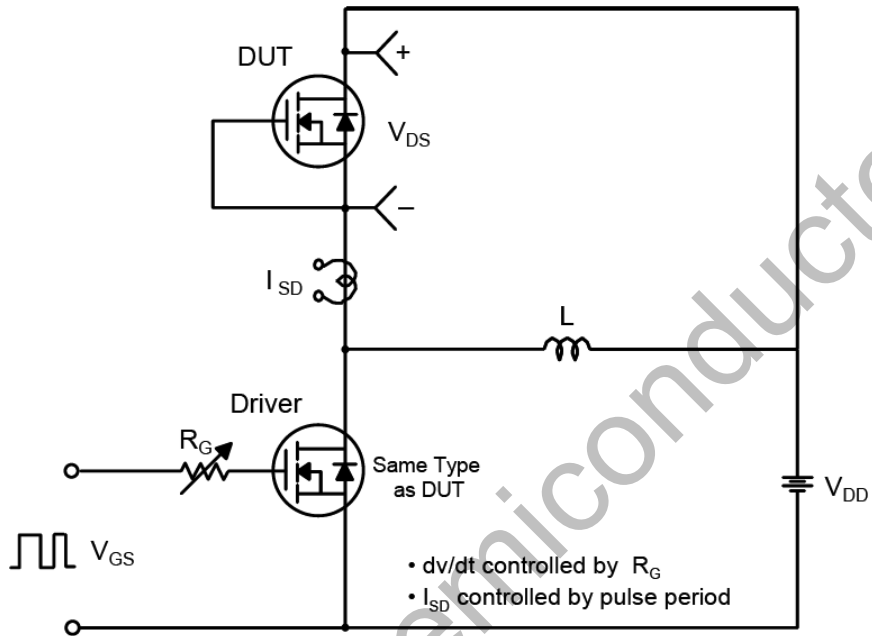
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveform



Package Dimension

TO-220

Unit: mm

